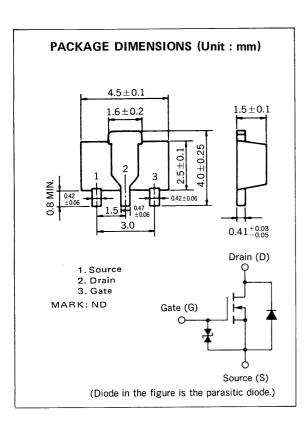


# MOS FIELD EFFECT TRANSISTOR **2SK1583**

# N-CHANNEL MOS FET FOR SWITCHING



The 2SK1583 is an N-channel vertical type MOS FET which can be driven by 2.5 V power supply.

As the MOS FET is driven by low voltage and does not require consideration of driving current, it is suitable for appliances including VCR cameras and headphone stereos which need power saving.

#### **FEATURES**

- Directly driven by ICs having a 3 V power supply.
- Has low on-state resistance

 $R_{DS(on)1}$  = 2.0  $\Omega$  MAX. @  $V_{GS}$  = 2.5 V,  $I_D$  = 0.3 A  $R_{DS(on)2}$  = 1.5  $\Omega$  MAX. @  $V_{GS}$  = 4.0 V,  $I_D$  = 0.3 A

#### QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

# ABSOLUTE MAXIMUM RATINGS ( $T_a = 25$ °C)

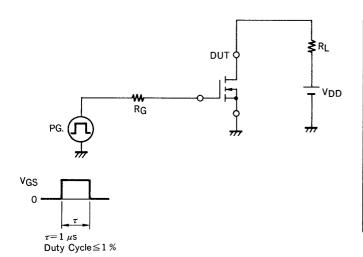
PARAMETER	SYMBOL	RATINGS	UNIT	TEST CONDITIONS
Drain to Source Voltage	V <sub>DSS</sub>	16	V	V <sub>GS</sub> = 0
Gate to Source Voltage	V <sub>GSS</sub>	±16	V	V <sub>DS</sub> = 0
Drain Current	ID(DC)	±0.5	Α	
Drain Current	I <sub>D</sub> (pulse)	±1.0	Α	PW $\leq$ 10 ms, Duty Cycle $\leq$ 50 %
Total Power Dissipation	PT	2.0	w	when using ceramic board of 16 cm² x 0.7 mm
Channel Temperature	T <sub>ch</sub>	150	°C	
Operating Temperature	T <sub>opt</sub>	-55 to +80	°C	
Storage Temperature	T <sub>stg</sub>	55 to +150	°C	

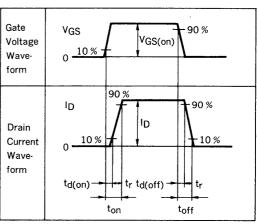


# ELECTRICL CHARACTERISTICS ( $T_a = 25$ °C)

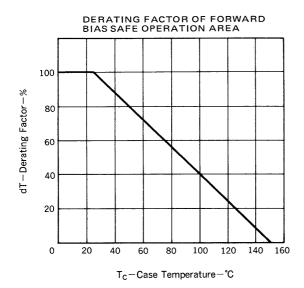
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Cut-off Current	IDSS			1.0	μΑ	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0
Gate Leakage Current	<sup>1</sup> GSS			±5.0	μА	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Gate Cut-off Voltage	VGS(off)	0.8	1.0	1.6	V	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 1 mA
Forward Transfer Admittance	ly <sub>fs</sub> !	400	550		mS	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 0.3 A
Drain to Source On-State Resistance	R <sub>DS(on)1</sub>		1.8	2.0	Ω	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.3 A
Drain to Source On-State Resistance	R <sub>DS(on)2</sub>		0.8	1.5	Ω	V <sub>GS</sub> = 4.0 V, I <sub>D</sub> = 0.3 A
Input Capacitance	Ciss		60		pF	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 0, f = 1 MHz
Output Capacitance	Coss		70		рF	
Feedback Capacitance	C <sub>rss</sub>		15		pF	
Turn-On Delay Time	<sup>t</sup> d(on)		95		ns	
Rise Time	t <sub>r</sub>		360		ns	$V_{GS(on)} = 3 \text{ V, R}_{G} = 10 \Omega$ $V_{DD} = 10 \text{ V, I}_{D} = 0.3 \text{ A}$ $R_{L} = 33 \Omega$
Turn-Off Delay Time	td(off)		160		ns	
Fall Time	tf		150		ns	

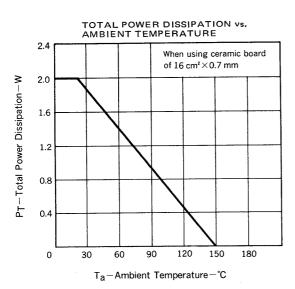
# SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS

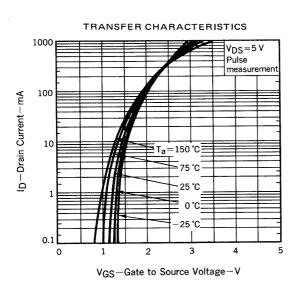


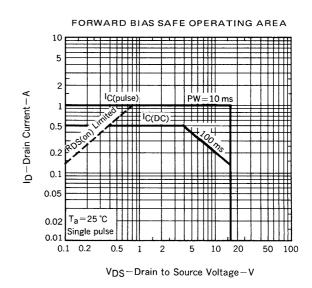


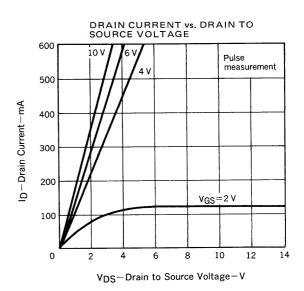
# TYPICAL CHARACTERISTICS (Ta = 25 °C)

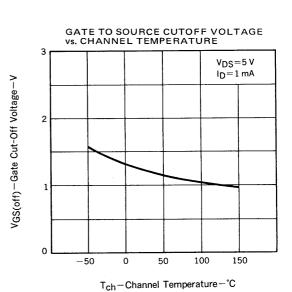


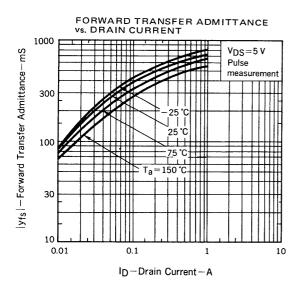




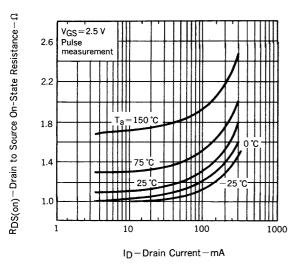


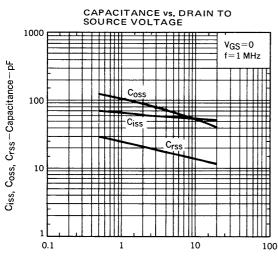




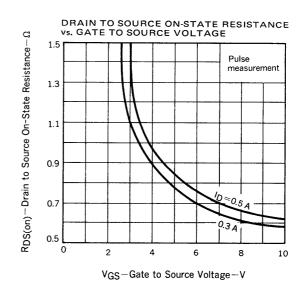


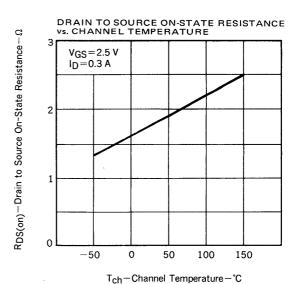
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

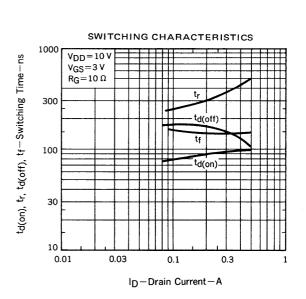


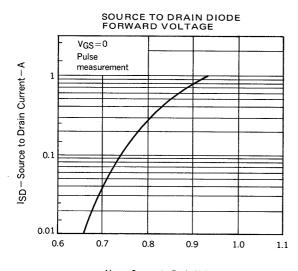


V<sub>DS</sub>-Drain to Source Voltage-V









#### V<sub>SD</sub>-Source to Drain Voltage-V

#### RECOMMENDED SOLDERING CONDITIONS

Mounting of this product by soldering should be done under the following conditions.

Please consult our representatives about soldering methods and conditions other than these.

### **SURFACE MOUNT TYPE**

For details of the recommended soldering conditions, see the information document.

"Device Mounting Manual for Surface Mounting (IEI-1207)."

Soldering Method	Soldering Conditions	Symbol for Recommended Conditions
Infrared Reflow	Package peak temp.: 230 °C Soldering time: within 30 sec (above 210 °C) Soldering times: 1, Days limitation: none*	IR30-00
Vapor Phase Soldering	Package peak temp.: 215 °C Soldering time: within 40 sec (above 200 °C) Soldering times: 1, Days limitation: none*	VP15-00
Wave Soldering	Soldering bath temp.: below 260 °C Soldering time: within 10 sec Soldering times: 1, Days limitation: none*	WS60-00

<sup>\*:</sup> Stored days under storage conditions at 25 °C and below 65 % R.H. after the dry-pack has been opened.

Note 1 Combination of soldering methods should be avoided.



#### REFERENCE

Document Name	Document No.	
NEC semiconductor device reliability/quality control system.	TEI-1202	
Quality grade on NEC semiconductor devices.	IEI-1209	
Semiconductor device mounting technology manual.	IEI-1207	
Semiconductor device package manual.	IEI-1213	
Guide to quality assurance for semiconductor devices.	MEI-1202	
Semiconductor selection guide.	MF-1134	

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Application examples recommended by NEC Corporation

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment,

Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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